TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

# TLP624,TLP624-2,TLP624-4

## Programmable Controllers AC/DC–Input Module

#### Telecommunication

The TOSHIBA TLP624, -2 and -4 consist of a gallium arsenide infrared emitting diode optically coupled to a photo-transistor.

The TLP624–2 offers two isolated channels in an eight lead plastic DIP, while the TLP624–4 provides four isolated channels in a sixteen plastic DIP.

- Collector-emitter voltage: 55V min.
- Current transfer ratio

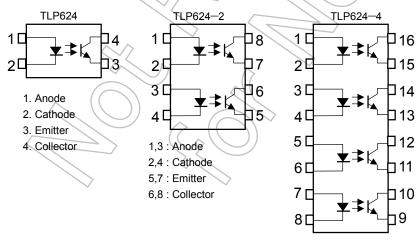
	Curre	o(min)	Marking \V	
Classi-	Ta =	25°C	Ta=-25~75°C	of
fication	I <sub>F</sub> =1mA	I <sub>F</sub> =0.5mA	I <sub>F</sub> =1mA	classi-
	V <sub>CE</sub> =0.5V	V <sub>CE</sub> =1.5V	V <sub>CE</sub> =0.5V	fication
Rank BV	200%	100%	100%	BV
Standard	100%	50%	50%	BV,blank

- Isolation voltage: 5000V<sub>rms</sub> min.
- UL recognized: UL1577, file No.E67349
- BSI approved: BS EN60065: 2002 Certificate No.7426 BS EN60950-1: 2002 Certificate No.7427
- Note: Application type name for certification test, please use
   standard product type name, i.e.

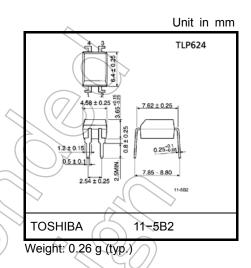
TLP624(BV): TLP624

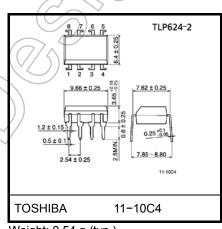
TLP624-2(BV): TLP624-2

## Pin Configurations (top view)

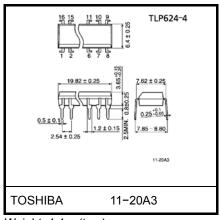


1,3,5,7: Anode 2,4,6,8: Cathode 9,11,13,15: Emitter 10,12,14,16: Collector





Weight: 0.54 g (typ.)



Weight: 1.1 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

				Ra		
	Characteristic		Symbol	TLP624 TLP624–2 TLP624–4		Unit
	Forward current		١ <sub>F</sub>	60	50	mA
	Forward current detating Pulse forward current		ΔI <sub>F</sub> / °C	–0.7(Ta ≥ 39°C)	–0.5(Ta ≥ 25°C)	mA / °C
			I <sub>FP</sub>	1(100µs, pu	lse, 100pps)	А
LED	Power dissipation(1 Circuit)		PD	100	70	mW
	Power dissipation derating (Ta ≥ 25°C, 1 Circuit)		ΔP <sub>D</sub> / °C	10	-0.7	mW / °C
	Reverse voltage		V <sub>R</sub>		5	V
	Junction temperature	temperature		125		°C
	Collector-emitter voltage		VCEO	55		V
	Emitter-collector voltage		VECO		7	V
tor	Collector current		Ic	5	0	mA
Detector	Collector power dissipation(1 circuit)		Pes	150	100	mW
	Collector power dissipation derating (Ta ≥ 25°C, 1 Circuit)	6	∆Pc1°C	-1.5	-1.0	mW / °C
	Junction temperature		Ťj	125		°C
Stor	age temperature range	$\sim$	∕ ⊤ <sub>stg</sub>	-55~125		°C
Ope	rating temperature range	$\sim \sim \sim$	P <sub>opr</sub>	-55~100		°C
Lead soldering temperature		$\sim$	T <sub>sol</sub>	260(10s)		°C
Tota	I package power dissipation(1 Circuit)		Рт	250	150	mW
	I package power dissipation derating ≥ 25°C, 1 Circuit)	$\checkmark$	ΔP <sub>T</sub> / °C	-2.5	-1.5	mW / °C
Isola	tion voltage	(Note 1)	BVS	5000(AC, 1m	in., RH≤60%)	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: LED side pins shorted together, and detector side pins shorted together.

## **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	5	24	V
Forward current	∕ I <sub>F</sub>	_	1.6	20	mA
Collector current	Ι <sub>C</sub>	_	1	10	mA
Operating temperature	T <sub>opr</sub>	-25		75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

## Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	VF	I <sub>F</sub> = 10mA	1.0	1.15	1.3	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5V		_	10	μA
	Capacitance	CT	V = 0, f = 1MHz	_ <	30	_	pF
	Collector–emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 0.5mA	55	$\langle \frown \rangle$		V
tor	Emitter–collector breakdown voltage	V <sub>(BR)ECO</sub>	I <sub>E</sub> = 0.1mA	6		_	V
Detector	Collector dark current	10-00	V <sub>CE</sub> = 24V	VY /	10	100	nA
		ICEO	V <sub>CE</sub> = 24V, Ta = 85°C	N.	2	50	μA
	Capacitance collector to emitter	C <sub>CE</sub>	V=0 , f=1MHz	$\mathcal{T}$	12	-	pF

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	$I_F = 1mA, V_{CE} = 0.5V$ Rank BV	100 200		1200 1200	%
Low input CTR	I <sub>C</sub> / I <sub>F</sub> (low)	$I_F = 0.5 \text{mA}, V_{CE} = 1.5 \text{V}$ Rank BV	50			%
	<	I <sub>C</sub> = 0.5mA, I <sub>F</sub> = 1mA	1	_	0.4	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 1mA, I <sub>F</sub> = 1mA		0.2	_	V
outuration voltago	(	Rank BV	//-	—	0.4	

## Coupled Electrical Characteristics (Ta = $-25^{\circ}C-75^{\circ}C$ )

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio		$I_F = 1$ mA, $V_{CE} = 0.5V$ Rank BV	50	_	_	%
	IC / IF		100	_	_	70
Low input CTR	IC / IF	I <sub>F</sub> = 0.5mA, V <sub>CE</sub> = 1.5V	_	50		%
	(low)	Rank BV	_	100	_	70

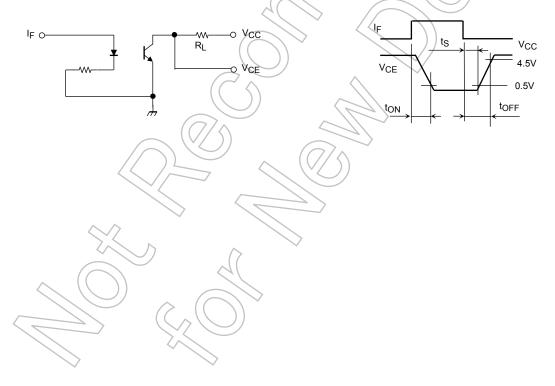
Isolation Characteristics (Ta = 25°C)

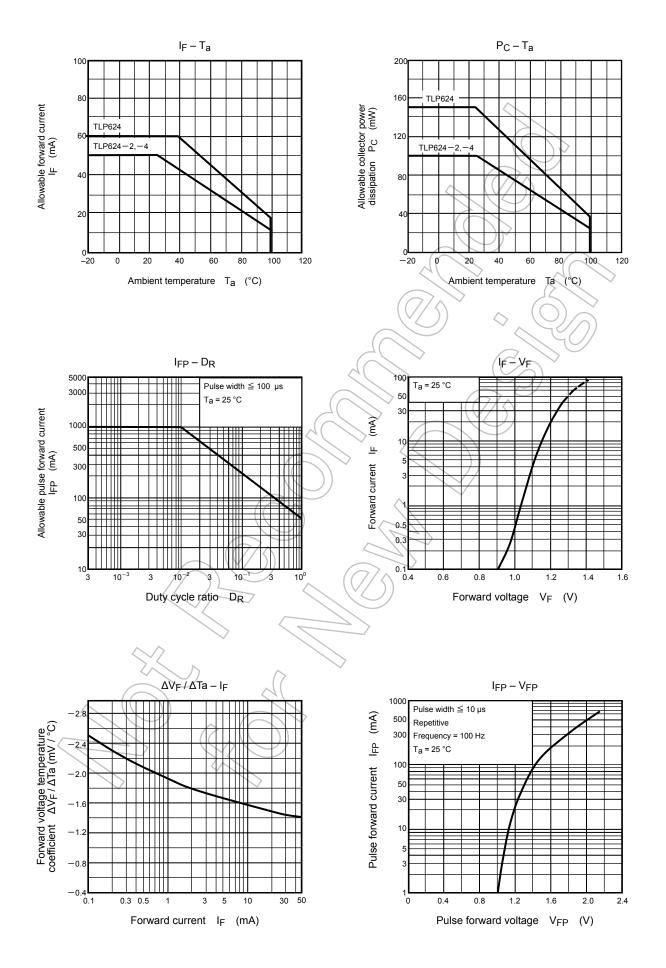
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V <sub>S</sub> = 0, f = 1MHz	—	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500V	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	BVS	AC, 1minute	5000 <	/		Vrms
		AC, 1second, in oil	—	10000	1	vinis
		DC, 1 minute, in oil	—	10000	)^_	Vdc

## Switching Characteristics (Ta = 25°C)

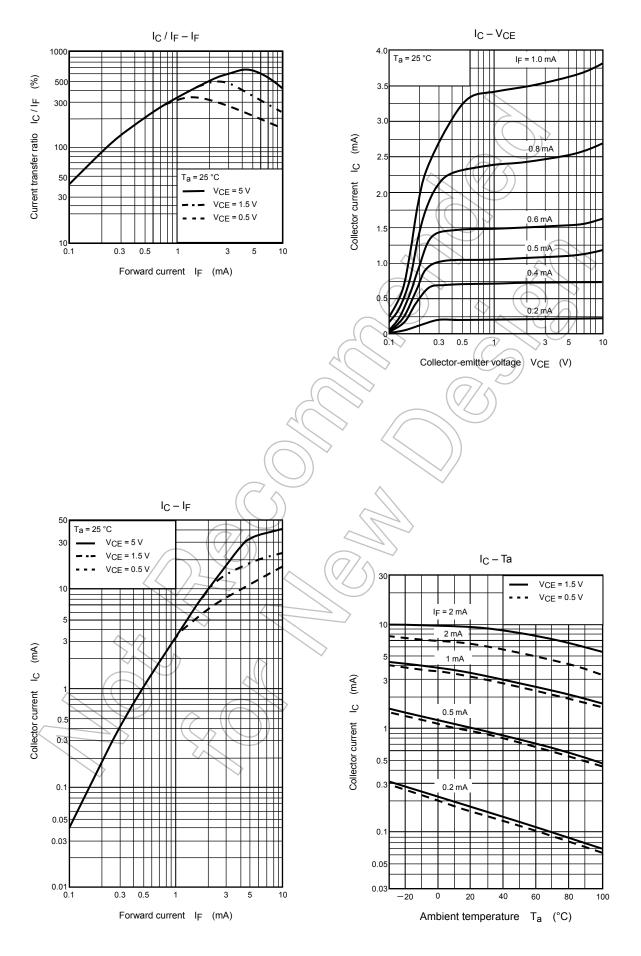
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	tr		_	8	$\square$	
Fall time	t <sub>f</sub>	$V_{CC} = 10V, I_C = 2mA$ $R_L = 100\Omega$	~_	8	SF.	$\rightarrow$
Turn-on time	t <sub>on</sub>		> _	10	$\overline{)}$	μs
Turn-off time	t <sub>off</sub>		_◇	8	1A	)
Turn-on time	t <sub>ON</sub>		-	10	Z	
Storage time	ts	R <sub>L</sub> = 4.7 kΩ (Fig.1) V <sub>CC</sub> = 5 V, I <sub>F</sub> = 1.6mA	-((	50	/ _	μs
Turn-off time	T <sub>OFF</sub>			300	_	

Fig. 1 Switching time test circuit

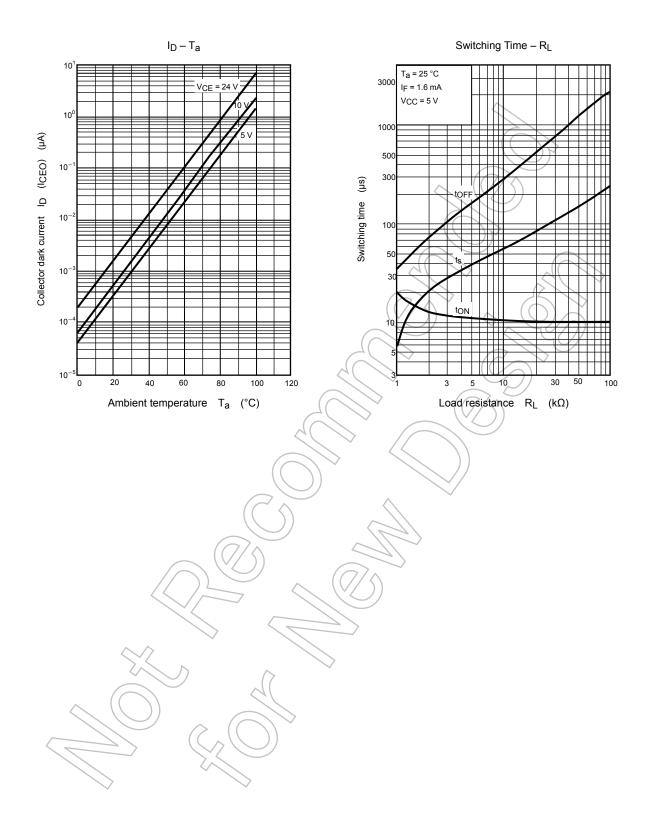




## **TOSHIBA**



# **TOSHIBA**



#### **RESTRICTIONS ON PRODUCT USE**

- Toshiba Corporation, and its subsidiaries and affiliates (collectively "TOSHIBA"), reserve the right to make changes to the information in this document, and related hardware, software and systems (collectively "Product") without notice.
- This document and any information herein may not be reproduced without prior written permission from TOSHIBA. Even with TOSHIBA's written permission, reproduction is permissible only if reproduction is without alteration/omission.
- Though TOSHIBA works continually to improve Product's quality and reliability, Product can malfunction or fail. Customers are responsible for complying with safety standards and for providing adequate designs and safeguards for their hardware, software and systems which minimize risk and avoid situations in which a malfunction or failure of Product could cause loss of human life, bodily injury or damage to property, including data loss or corruption. Before creating and producing designs and using, customers must also refer to and comply with (a) the latest versions of all relevant TOSHIBA information, including without limitation, this document, the specifications, the data sheets and application notes for Product and the precautions and conditions set forth in the "TOSHIBA Semiconductor Reliability Handbook" and (b) the instructions for the application that Product will be used with or for. Customers are solely responsible for all aspects of their own product design or applications, including but not limited to (a) determining the appropriateness of the use of this Product in such design or applications; (b) evaluating and determining the applicability of any information contained in this document, or in charts, diagrams, programs, algorithms, sample application circuits, or any other referenced documents; and (c) validating all operating parameters for such designs and applications. TOSHIBA ASSUMES NO LIABILITY FOR CUSTOMERS' PRODUCT DESIGN OR APPLICATIONS.
- Product is intended for use in general electronics applications (e.g., computers, personal equipment, office equipment, measuring equipment, industrial robots and home electronics applications or for specific applications as expressly stated in this document. Product is neither intended nor warranted for use in equipment or systems that require extraordinarily high levels of quality and/or reliability and/or a malfunction or failure of which may cause loss of human life, bodily injury, serious property damage or serious public impact ("Unintended Use"). Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in the aerospace industry, medical equipment, equipment used for automobiles, trains, ships and other transportation, traffic signaling equipment, equipment used to control combustions or explosions, safety devices, elevators and escalators, devices related to electric power, and equipment used in finance-related fields. Do not use Product for Unintended Use unless specifically permitted in this document.
- · Do not disassemble, analyze, reverse-engineer, alter, modify, translate or copy Product, whether in whole or in part.
- Product shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any
  applicable laws or regulations.
- The information contained herein is presented only as guidance for Product use. No responsibility is assumed by TOSHIBA for any
  infringement of patents or any other intellectual property rights of third parties that may result from the use of Product. No license to
  any intellectual property right is granted by this document, whether express or implied, by estoppel or otherwise.
- ABSENT A WRITTEN SIGNED AGREEMENT, EXCEPT AS PROVIDED IN THE RELEVANT TERMS AND CONDITIONS OF SALE FOR PRODUCT, AND TO THE MAXIMUM EXTENT ALLOWABLE BY LAW, TOSHIBA (1) ASSUMES NO LIABILITY WHATSOEVER, INCLUDING WITHOUT LIMITATION, INDIRECT, CONSEQUENTIAL, SPECIAL, OR INCIDENTAL DAMAGES OR LOSS, INCLUDING WITHOUT LIMITATION, LOSS OF PROFITS, LOSS OF OPPORTUNITIES, BUSINESS INTERRUPTION AND LOSS OF DATA, AND (2) DISCLAIMS ANY AND ALL EXPRESS OR IMPLIED WARRANTIES AND CONDITIONS RELATED TO SALE, USE OF PRODUCT, OR INFORMATION, INCLUDING WARRANTIES OR CONDITIONS OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, ACCURACY OF INFORMATION, OR NONINFRINGEMENT.
- GaAs (Gallium Arsenide) is used in Product. GaAs is harmful to humans if consumed or absorbed, whether in the form of dust or vapor. Handle with care and do not break, cut, crush, grind, dissolve chemically or otherwise expose GaAs in Product.
- Do not use or otherwise make available Product or related software or technology for any military purposes, including without
  limitation, for the design, development, use, stockpiling or manufacturing of nuclear, chemical, or biological weapons or missile
  technology products (mass destruction weapons). Product and related software and technology may be controlled under the
  Japanese Foreign Exchange and Foreign Trade Law and the U.S. Export Administration Regulations. Export and re-export of Product
  or related software or technology are strictly prohibited except in compliance with all applicable export laws and regulations.
- Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. Please use Product in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. TOSHIBA assumes no liability for damages or losses occurring as a result of noncompliance with applicable laws and regulations.